



Low-Voltage, Low r_{ON} , SPDT Audio Switch with Negative Swing Capability

DESCRIPTION

The DG2612/2613 is a low on-resistance, single-pole/double-throw monolithic CMOS analog switch with negative signal swing capability. It is designed for low voltage applications. The DG2612/2613 is ideal for portable and battery powered equipment, requiring high performance and efficient use of board space. In addition to the low on-resistance ($1.0\ \Omega$ at 2.7 V), the DG2613 has a typical OFF Isolation and Crosstalk of -67 dB and -73 dB respectively.

The DG2612/2613 is built on Vishay Siliconix's low voltage process.

Break-before-make is guaranteed.

As a committed partner to the community and the environment, Vishay Siliconix manufactures this product with the lead (Pb)-free device terminations. For analog switching products manufactured with 100 % matte tin device terminations, the lead (Pb)-free "-E3" suffix is being used as a designator.

FEATURES

- Low Voltage Operation (1.8 V to 5.5 V)
- Low On-Resistance - r_{ON} : $1.0\ \Omega$ at 2.7 V
- High Bandwidth



RoHS
COMPLIANT

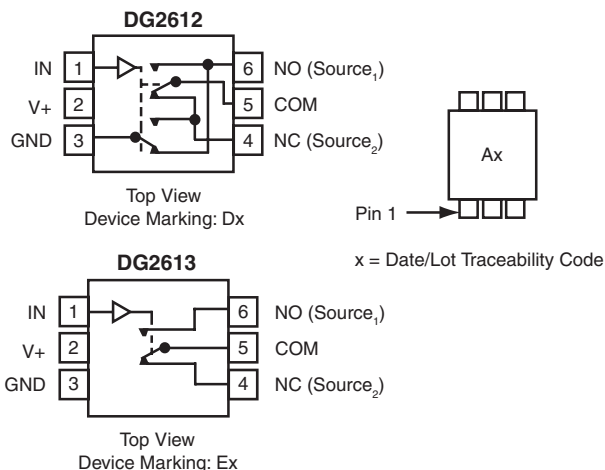
BENEFITS

- Negative Signal Swing Capability
- Shunt Switch to Eliminate Switching Noise
- Simplified Design with Direct DC Coupling
- Space Saving SC-89 Package

APPLICATIONS

- Cellular Phones
- Portable Multimedia Players
- PDAs and Hand-held Devices
- Laptop Computers

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



TRUTH TABLE

Logic	NC	NO
0	ON	OFF
1	OFF	ON

COMMERCIAL ORDERING INFORMATION

Temp Range	Package	Part Number
-40 to 85 °C	SC-89 (SOT-666) Lead (Pb)-free with Tape and Reel	DG2612DX-T1-E3 DG2613DX-T1-E3

ABSOLUTE MAXIMUM RATINGS $T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted

Parameter	Symbol	Limit	Unit
Reference V_+ to GND		-0.3 to +6	V
IN, COM, NC, NO ^a		-0.3 to ($V_+ + 0.3\text{ V}$)	
Continuous Current (NO, NC, COM pins)		± 150	mA
Peak Current (Pulsed at 1 ms, 10 % duty cycle)		± 300	
Storage Temperature	D Suffix	-65 to 150	$^{\circ}\text{C}$
Power Dissipation (Packages) ^b	SC-89 ^c	172	mW

Notes:

a. Signals on NC, NO, or COM or IN exceeding V_+ will be clamped by internal diodes. Limit forward diode current to maximum current ratings.

b. All leads welded or soldered to PC Board.

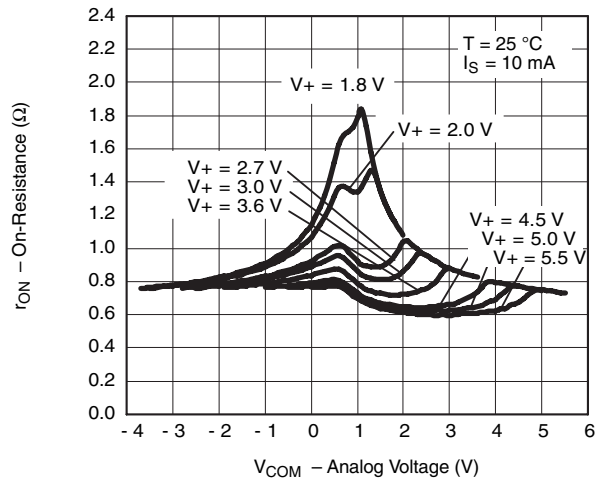
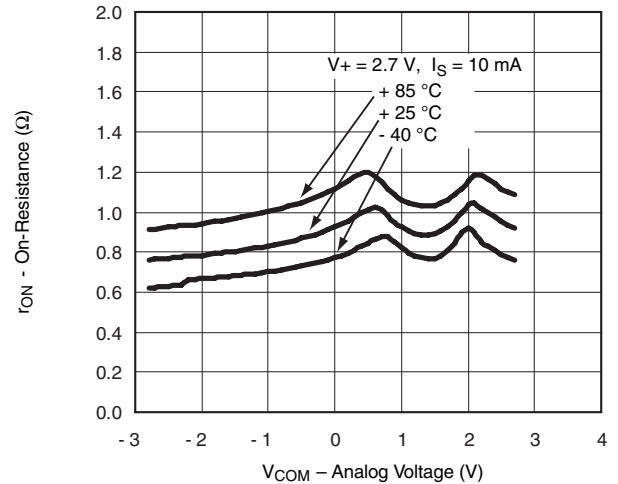
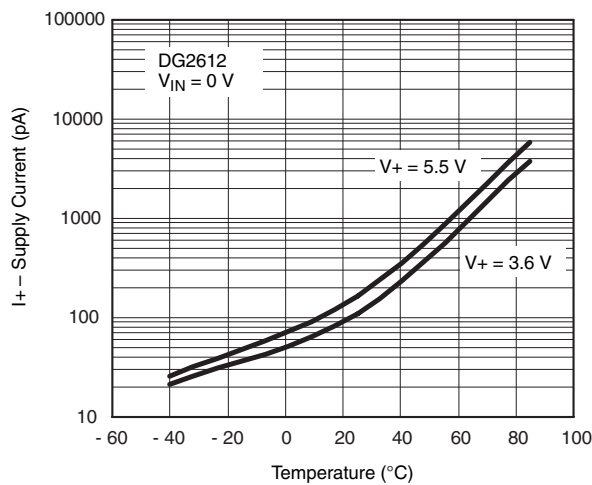
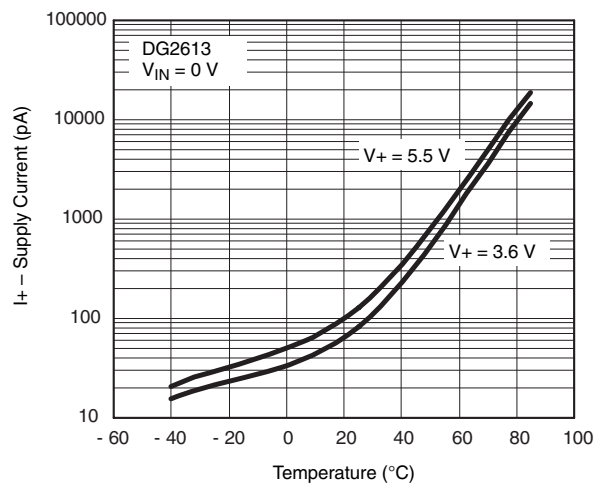
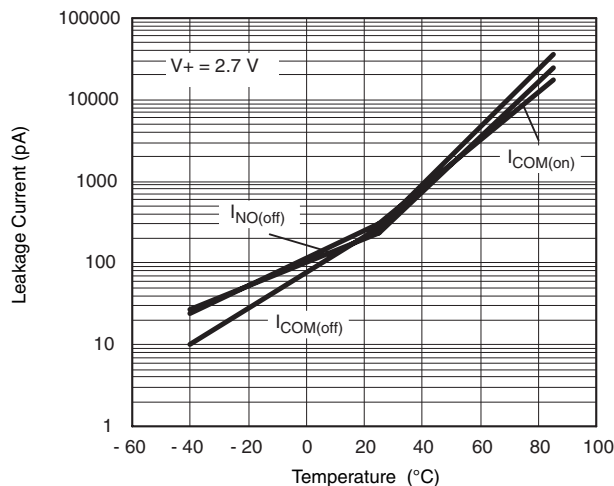
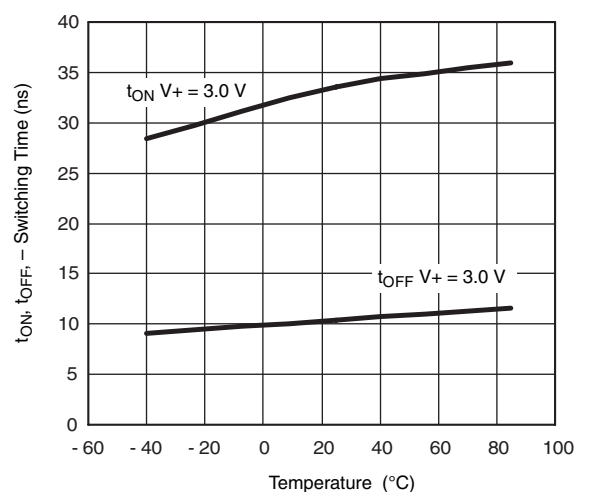
c. Derate 2.15 mW/ $^{\circ}\text{C}$ above $70\text{ }^{\circ}\text{C}$.

SPECIFICATIONS (V+ = 3 V)							
Parameter	Symbol	Test Conditions Otherwise Unless Specified V+ = 3 V, ± 10 %, V _{IN} = 0.5 V or 1.4 V ^e	Temp ^a	Limits - 40 to 85 °C			Unit
				Min ^b	Typ ^c	Max ^b	
Analog Switch							
Analog Signal Range ^d	V _{NO} , V _{NC} , V _{COM}		Full	0		V+	V
On-Resistance	r _{ON}	V+ = 2.7 V, V _{COM} = - 1 V/0 V/1 V/2 V I _{NO} , I _{NC} = 10 mA	Room		1.0	1.4	Ω
r _{ON} Match ^d	Δr _{ON}		Full			1.6	
r _{ON} Flatness ^d	r _{ON} Flatness		Room			0.1	
Shunt Switch Resistance	R _{SH}	I _{NO} or I _{NC} = 10 mA, V+ = 2.7 V, DG2612 only	Room		150	300	Ω
Switch Off Leakage Current	I _{NO(off)} I _{NC(off)}	V+ = 3.3 V, V _{NO} , V _{NC} = 1 V/3 V, V _{COM} = 3 V/1 V	Full	- 2 - 100		2 100	nA
	I _{COM(off)}		Room	- 2 - 100		2 100	
Channel-On Leakage Current	I _{COM(on)}	V+ = 3.3 V, V _{NO} , V _{NC} = V _{COM} = 1 V/3 V	Full	- 2 - 100		2 100	
Digital Control							
Input High Voltage	V _{INH}	V+ = 1.8 V to 2.0 V	Full	1.0			V
		V+ = 2.7 V to 3.6 V		1.4			
		V+ = 4.2 V to 5.5 V		2.0			
Input Low Voltage	V _{INL}	V+ = 1.8 V to 2.0 V				0.4	
		V+ = 2.7 V to 3.6 V				0.5	
		V+ = 4.2 V to 5.5 V				0.8	
Input Capacitance	C _{in}		Full		5		pF
Input Current	I _{INL} or I _{INH}	V _{IN} = 0 or V+	Full	1		1	μA
Dynamic Characteristics							
Turn-On Time	t _{ON}	V _{NO} or V _{NC} = 1.5 V, R _L = 50 Ω, C _L = 35 pF	Room		34	60	ns
Turn-Off Time	t _{OFF}		Full		10	35	
Break-Before-Make Time	t _{BBM}		Room	4	16	37	
Charge Injection ^d (DG2613)	Q _{INJ}	C _L = 1 nF, V _{GEN} = 0 V, R _{GEN} = 0 Ω	Room		2.4		pC
Off-Isolation ^d	OIRR	R _L = 50 Ω, C _L = 5 pF, f = 100 kHz	Room		- 61		dB
Crosstalk ^d	X _{TALK}	DG2612	Room		- 67		
Off-Isolation ^d	OIRR	R _L = 50 Ω, C _L = 5 pF, f = 100 kHz	Room		- 67		dB
Crosstalk ^d	X _{TALK}	DG2613	Room		- 73		
N _O , N _C Off Capacitance ^d	C _{NO(off)} C _{NC(off)}	V _{IN} = 0 or V+, f = 1 MHz	Room		36		pF
Channel-On Capacitance ^d	C _{ON}		Room		95		
Power Supply							
Power Supply Range	V+			1.8		5.5	V
Power Supply Current	I+	V _{IN} = 0 or V+			0.01	1.0	μA

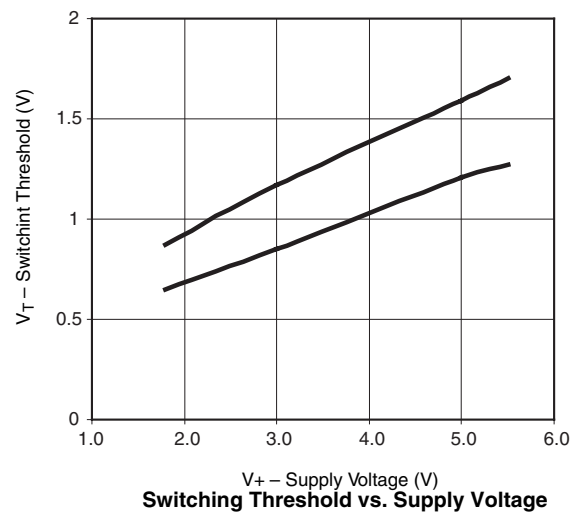
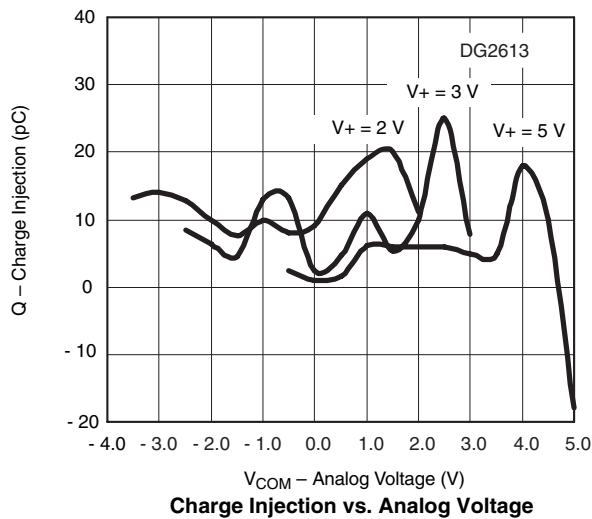
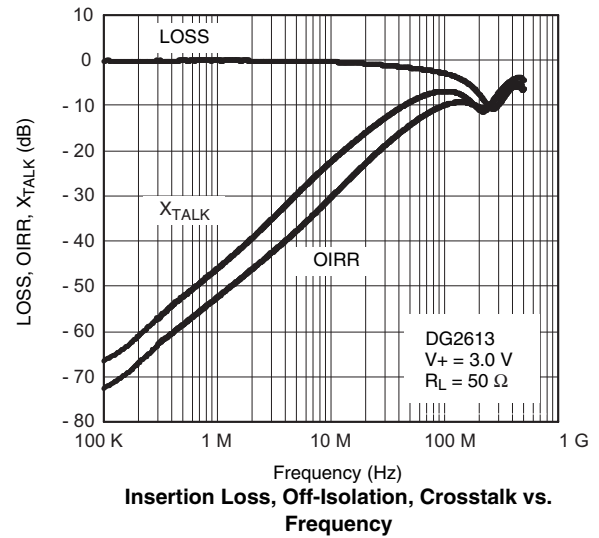
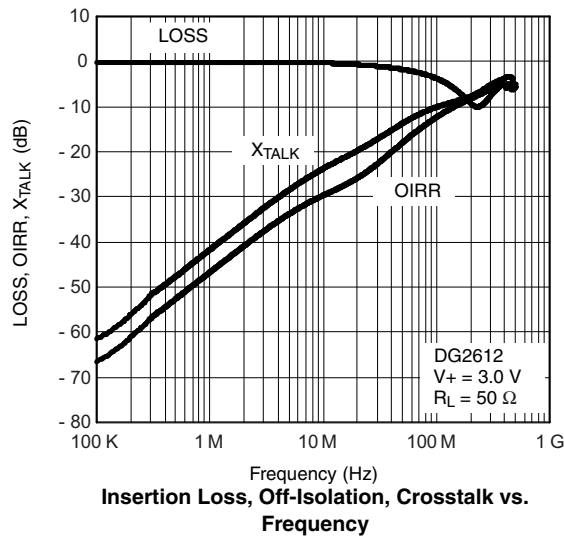
Notes:

- Room = 25 °C, Full = as determined by the operating suffix.
- Typical values are for design aid only, not guaranteed nor subject to production testing.
- The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
- Guarantee by design, nor subjected to production test.
- V_{IN} = input voltage to perform proper function.
- Guaranteed by 5 V leakage testing, not production tested.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS $T_A = 25^\circ\text{C}$, unless otherwise noted

 r_{ON} vs. V_{COM} and Supply Voltage

 r_{ON} vs. Analog Voltage and Temperature

Supply Current vs. Temperature

Supply Current vs. Temperature

Leakage Current vs. Temperature

Switching Time vs. Temperature and Supply Voltage

TYPICAL CHARACTERISTICS $T_A = 25^\circ\text{C}$, unless otherwise noted



TEST CIRCUITS

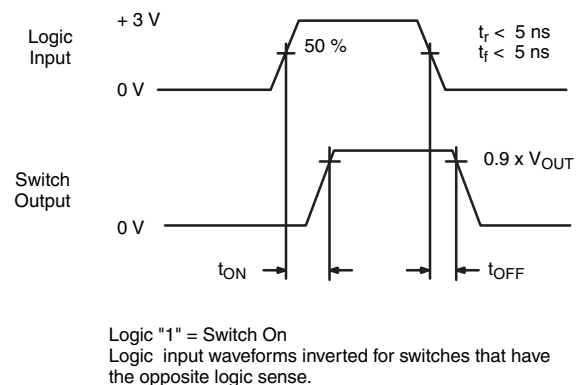
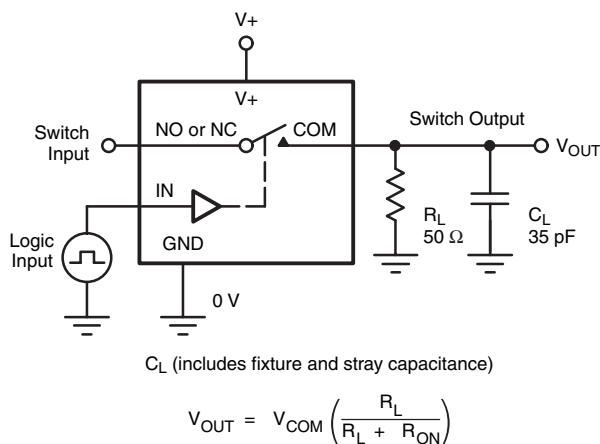
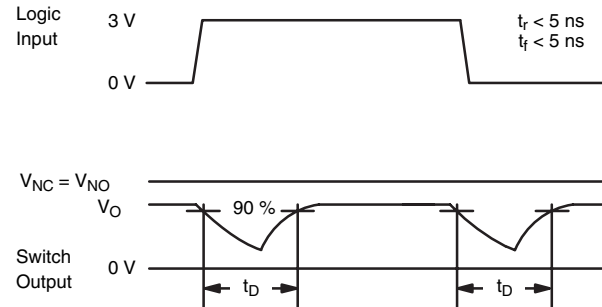
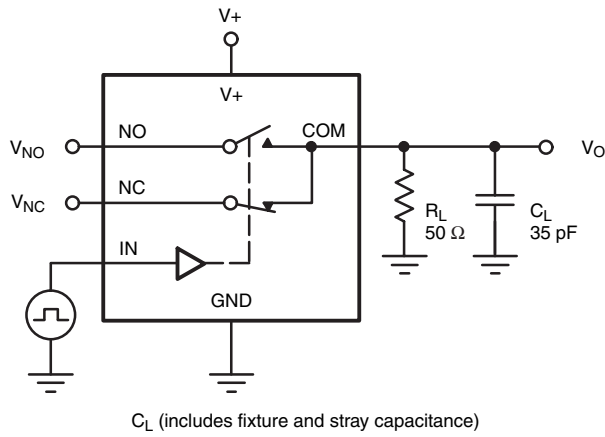
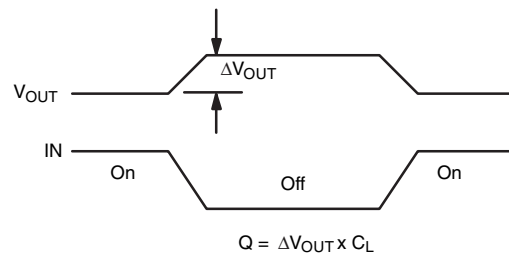
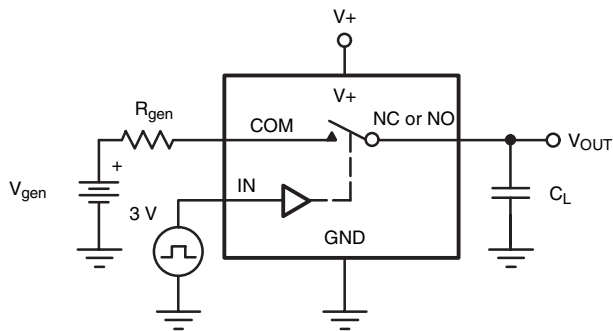
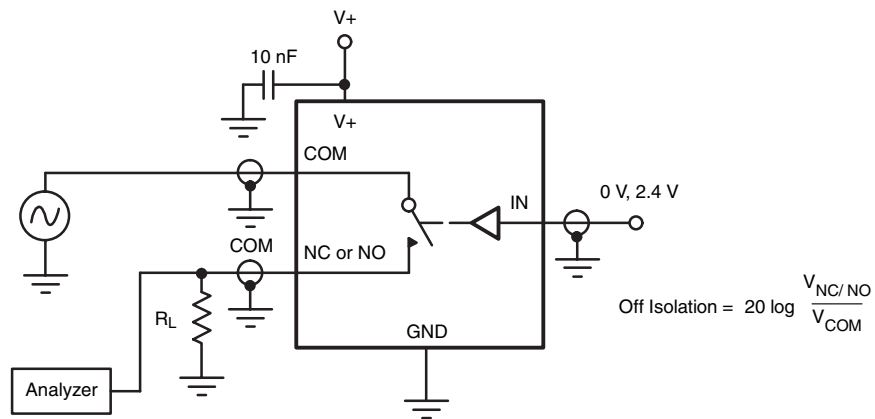


Figure 1. Switching Time

TEST CIRCUITS

Figure 2. Break-Before-Make Interval


IN depends on switch configuration: input polarity determined by sense of switch.

Figure 3. Charge Injection

Figure 4. Off-Isolation

TEST CIRCUITS

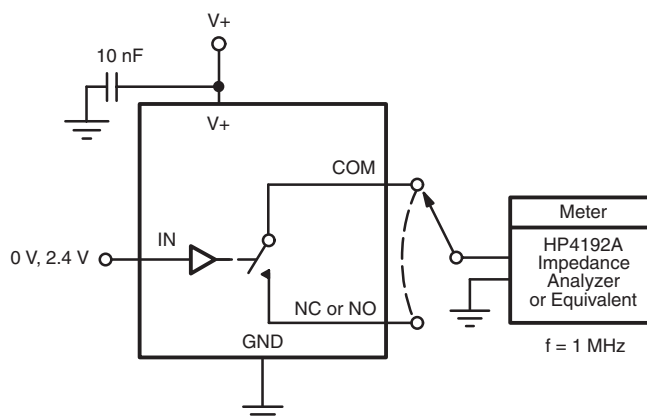


Figure 5. Channel Off/On Capacitance

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <http://www.vishay.com/ppg?74339>.



Notice

Specifications of the products displayed herein are subject to change without notice. Vishay Intertechnology, Inc., or anyone on its behalf, assumes no responsibility or liability for any errors or inaccuracies.

Information contained herein is intended to provide a product description only. No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document. Except as provided in Vishay's terms and conditions of sale for such products, Vishay assumes no liability whatsoever, and disclaims any express or implied warranty, relating to sale and/or use of Vishay products including liability or warranties relating to fitness for a particular purpose, merchantability, or infringement of any patent, copyright, or other intellectual property right.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications. Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Vishay for any damages resulting from such improper use or sale.